

# BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

## Darlington Complementary Silicon Power Transistors

These devices are designed for general purpose and low speed switching applications.

### Features

- High DC Current Gain –  $h_{FE} = 2500$  (typ.) at  $I_C = 4.0$
- Collector–Emitter Sustaining Voltage at 100 mAdc  
 $V_{CEO(sus)} = 80$  Vdc (min) – BDX33B, BDX334B  
 $= 100$  Vdc (min) – BDX33C, BDX334C
- Low Collector–Emitter Saturation Voltage  
 $V_{CE(sat)} = 2.5$  Vdc (max) at  $I_C = 3.0$  Adc  
– BDX33B, 33C/34B, 34C
- Monolithic Construction with Build-In Base–Emitter Shunt Resistors
- These Devices are Pb–Free and are RoHS Compliant\*

### MAXIMUM RATINGS

| Rating                                                                                 | Symbol         | Value       | Unit                     |
|----------------------------------------------------------------------------------------|----------------|-------------|--------------------------|
| Collector–Emitter Voltage<br>BDX33B, BDX34B<br>BDX33C, BDX34C                          | $V_{CEO}$      | 80<br>100   | Vdc                      |
| Collector–Base Voltage<br>BDX33B, BDX34B<br>BDX33C, BDX34C                             | $V_{CB}$       | 80<br>100   | Vdc                      |
| Emitter–Base Voltage                                                                   | $V_{EB}$       | 5.0         | Vdc                      |
| Collector Current<br>Continuous<br>Peak                                                | $I_C$          | 10<br>15    | Adc                      |
| Base Current                                                                           | $I_B$          | 0.25        | Adc                      |
| Total Device Dissipation @ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$          | 70<br>0.56  | W<br>W/ $^\circ\text{C}$ |
| Operating and Storage Junction<br>Temperature Range                                    | $T_J, T_{stg}$ | –65 to +150 | $^\circ\text{C}$         |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

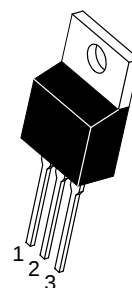
| Characteristics                      | Symbol          | Max  | Unit                      |
|--------------------------------------|-----------------|------|---------------------------|
| Thermal Resistance, Junction–to–Case | $R_{\theta JC}$ | 1.78 | $^\circ\text{C}/\text{W}$ |



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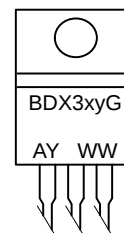
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## DARLINGTON 10 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 80–100 VOLTS, 65 WATTS



TO-220  
CASE 221A  
STYLE 1

### MARKING DIAGRAM



BDX3xy = Device Code  
x = 3 or 4  
y = B or C  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb–Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

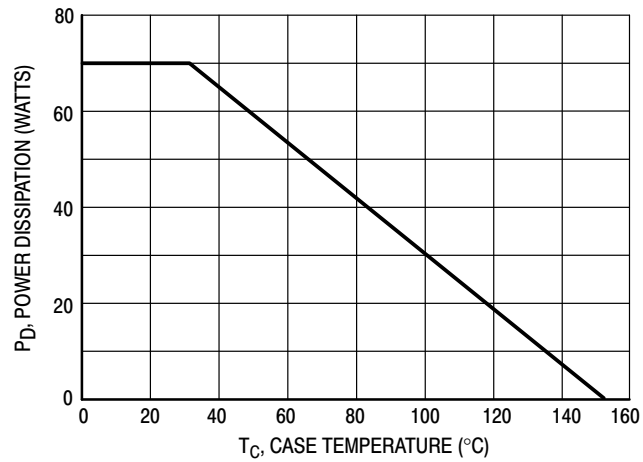


Figure 1. Power Derating

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

| Characteristic                                                                                                              |                                                 | Symbol                | Min       | Max        | Unit |
|-----------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------|-----------------------|-----------|------------|------|
| <b>OFF CHARACTERISTICS</b>                                                                                                  |                                                 |                       |           |            |      |
| Collector-Emitter Sustaining Voltage (Note 1)<br>(I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)                            | BDX33B/BDX34B<br>BDX33C/BDX34C                  | V <sub>CEO(sus)</sub> | 80<br>100 | –<br>–     | Vdc  |
| Collector-Emitter Sustaining Voltage (Note 1)<br>(I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0, R <sub>BE</sub> = 100)     | BDX33B/BDX34B<br>BDX33C/BDX33C                  | V <sub>CER(sus)</sub> | 80<br>100 | –<br>–     | Vdc  |
| Collector-Emitter Sustaining Voltage (Note 1)<br>(I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0, V <sub>BE</sub> = 1.5 Vdc) | BDX33B/BDX34B<br>BDX33C/BDX34C                  | V <sub>CEX(sus)</sub> | 80<br>100 | –<br>–     | Vdc  |
| Collector Cutoff Current<br>(V <sub>CE</sub> = 1/2 rated V <sub>CEO</sub> , I <sub>B</sub> = 0)                             | T <sub>C</sub> = 25°C<br>T <sub>C</sub> = 100°C | I <sub>CEO</sub>      | –<br>–    | 0.5<br>10  | mAdc |
| Collector Cutoff Current<br>(V <sub>CB</sub> = rated V <sub>CBO</sub> , I <sub>E</sub> = 0)                                 | T <sub>C</sub> = 25°C<br>T <sub>C</sub> = 100°C | I <sub>CBO</sub>      | –<br>–    | 1.0<br>5.0 | mAdc |
| Emitter Cutoff Current<br>(V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)                                                   |                                                 | I <sub>EBO</sub>      | –         | 10         | mAdc |
| <b>ON CHARACTERISTICS</b>                                                                                                   |                                                 |                       |           |            |      |
| DC Current Gain (Note 1)<br>(I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 3.0 Vdc)                                           | BDX33B, 33C/34B, 34C                            | h <sub>FE</sub>       | 750       | –          | –    |
| Collector-Emitter Saturation Voltage<br>(I <sub>C</sub> = 3.0 Adc, I <sub>B</sub> = 6.0 mAdc)                               | BDX33B, 33C/34B, 34C                            | V <sub>CE(sat)</sub>  | –         | 2.5        | Vdc  |
| Base-Emitter On Voltage<br>(I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 3.0 Vdc)                                            | BDX33B, 33C/34B, 34C                            | V <sub>BE(on)</sub>   | –         | 2.5        | Vdc  |
| Diode Forward Voltage<br>(I <sub>C</sub> = 8.0 Adc)                                                                         |                                                 | V <sub>F</sub>        | –         | 4.0        | Vdc  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. Pulse Test non repetitive: Pulse Width = 0.25 seconds.

# BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

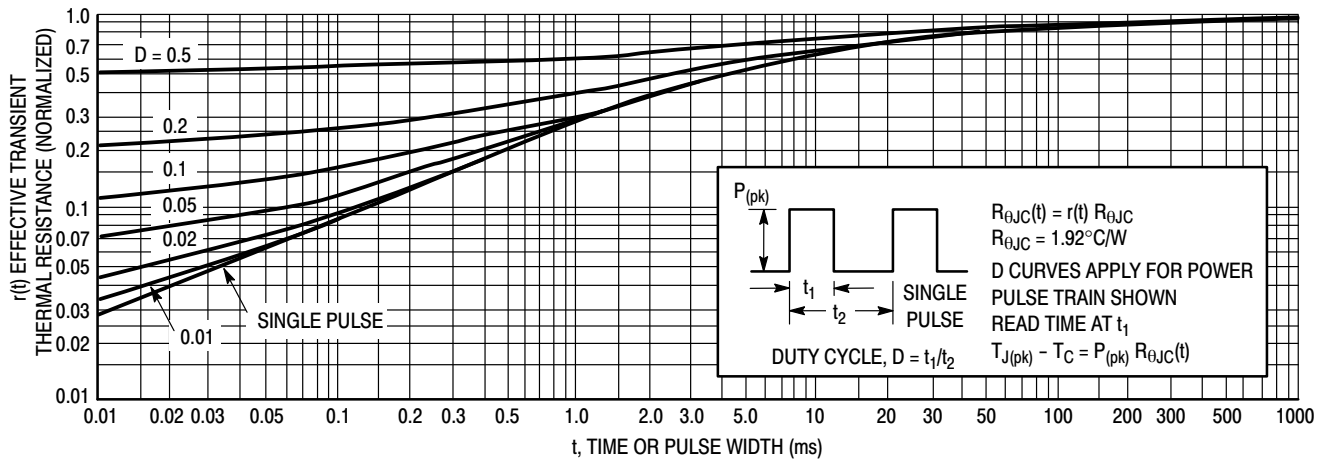


Figure 1. Thermal Response

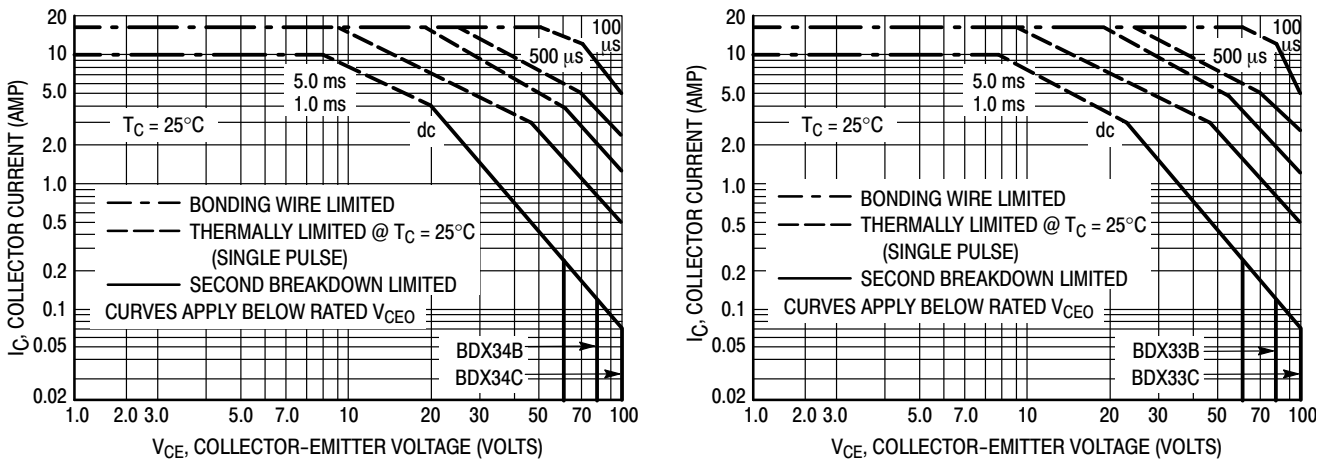


Figure 2. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 3 is based on  $T_{J(pk)}$

$= 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} = 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

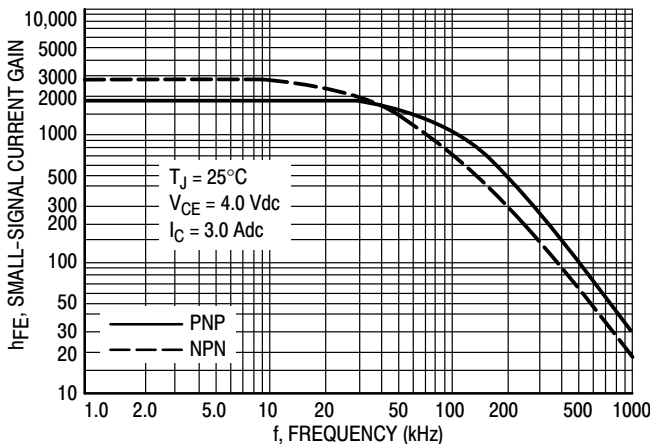


Figure 3. Small-Signal Current Gain

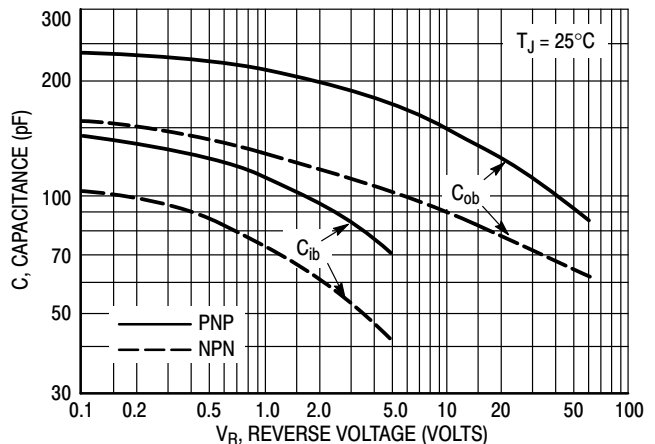
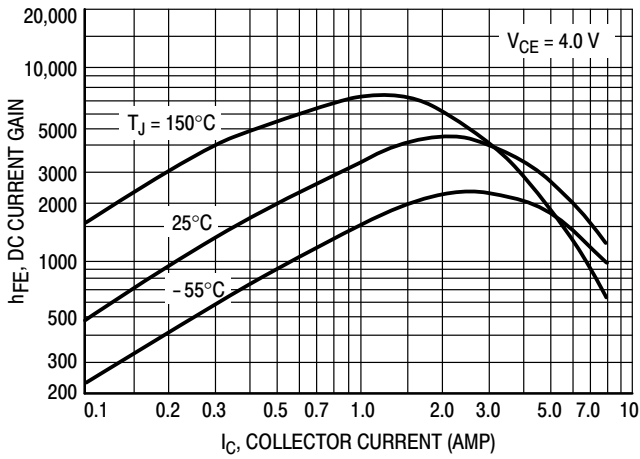


Figure 4. Capacitance

# BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

**NPN**  
**BDX33B, 33C**



**PNP**  
**BDX34B, 34C**

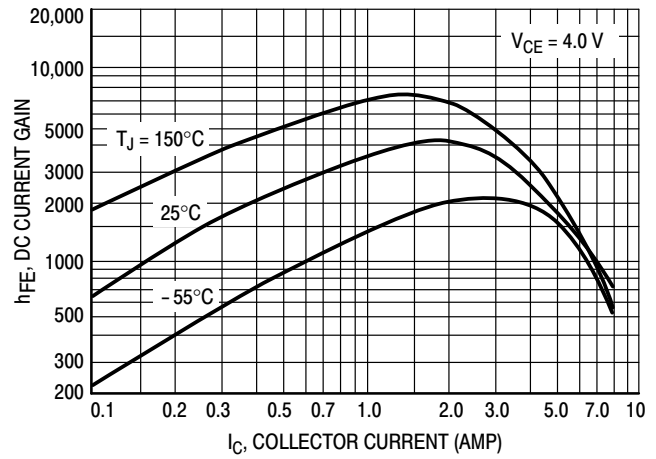


Figure 5. DC Current Gain

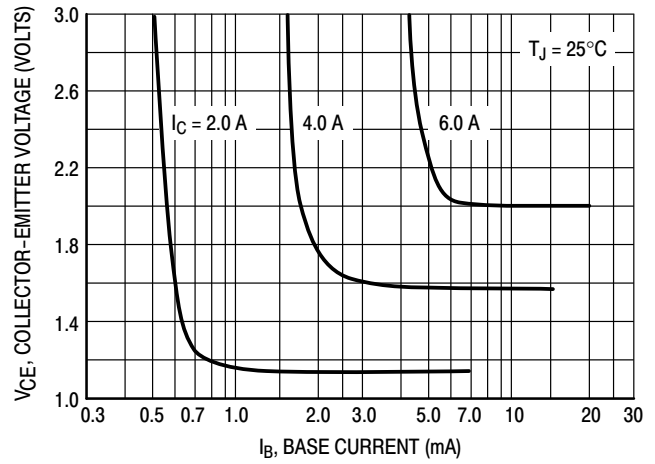
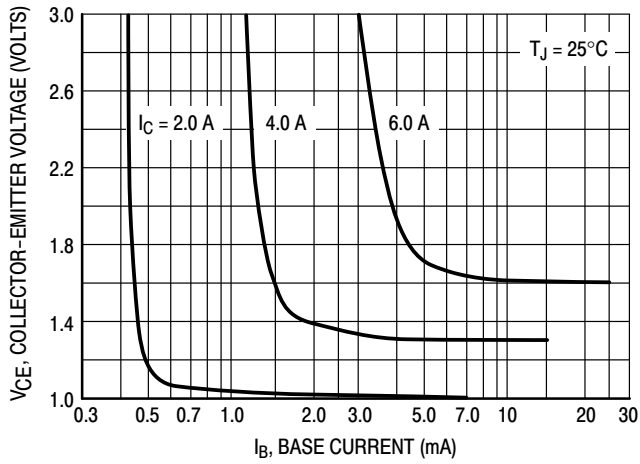


Figure 6. Collector Saturation Region

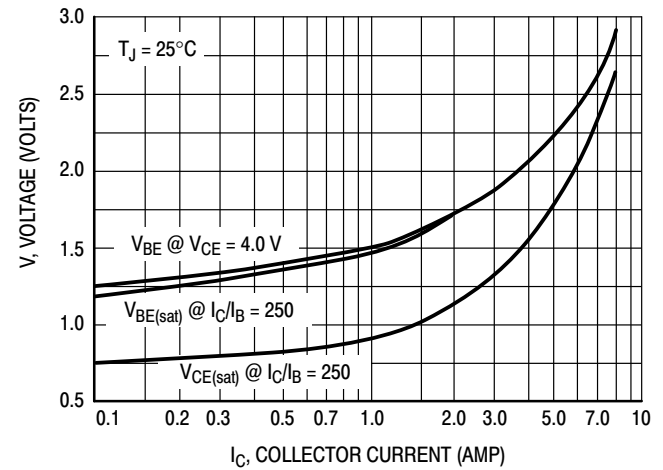
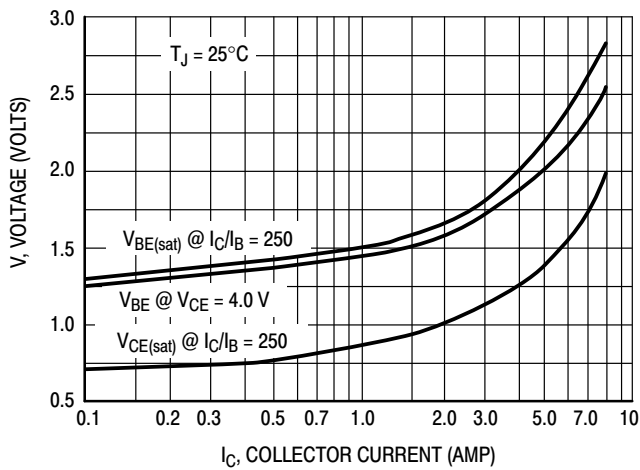


Figure 7. "On" Voltages

## BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

### ORDERING INFORMATION

| Device  | Package             | Shipping <sup>†</sup> |
|---------|---------------------|-----------------------|
| BDX33BG | TO-220<br>(Pb-Free) | 50 Units / Rail       |
| BDX33CG | TO-220<br>(Pb-Free) | 50 Units / Rail       |
| BDX34BG | TO-220<br>(Pb-Free) | 50 Units / Rail       |
| BDX34CG | TO-220<br>(Pb-Free) | 50 Units / Rail       |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



## TO-220 CASE 221A ISSUE AK

DATE 13 JAN 2022



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN.   | MAX.  | MIN.        | MAX.  |
| A   | 0.570  | 0.620 | 14.48       | 15.75 |
| B   | 0.380  | 0.415 | 9.66        | 10.53 |
| C   | 0.160  | 0.190 | 4.07        | 4.83  |
| D   | 0.025  | 0.038 | 0.64        | 0.96  |
| F   | 0.142  | 0.161 | 3.60        | 4.09  |
| G   | 0.095  | 0.105 | 2.42        | 2.66  |
| H   | 0.110  | 0.161 | 2.80        | 4.10  |
| J   | 0.014  | 0.024 | 0.36        | 0.61  |
| K   | 0.500  | 0.562 | 12.70       | 14.27 |
| L   | 0.045  | 0.060 | 1.15        | 1.52  |
| N   | 0.190  | 0.210 | 4.83        | 5.33  |
| Q   | 0.100  | 0.120 | 2.54        | 3.04  |
| R   | 0.080  | 0.110 | 2.04        | 2.79  |
| S   | 0.045  | 0.055 | 1.15        | 1.41  |
| T   | 0.235  | 0.255 | 5.97        | 6.47  |
| U   | 0.000  | 0.050 | 0.00        | 1.27  |
| V   | 0.045  | ----  | 1.15        | ---   |
| Z   | ----   | 0.080 | ---         | 2.04  |

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR  
4. EMITTER

STYLE 3:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 4:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

STYLE 5:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 6:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 7:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 8:  
PIN 1. CATHODE  
2. ANODE  
3. EXTERNAL TRIP/DELAY  
4. ANODE

STYLE 9:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 10:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN  
4. SOURCE

STYLE 11:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE  
4. SOURCE

STYLE 12:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. NOT CONNECTED

|                  |             |                                                                                                                                                                                     |
|------------------|-------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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